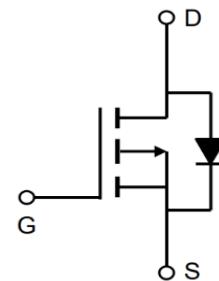
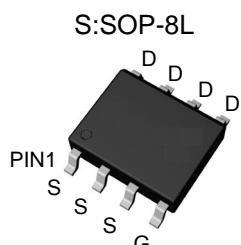
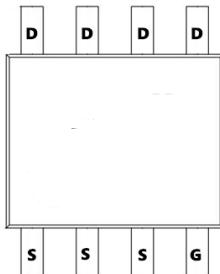


TM4907

P-Channel Enhancement Mosfet

General Description <ul style="list-style-type: none"> Low $R_{DS(ON)}$ RoHS and Halogen-Free Compliant Applications <ul style="list-style-type: none"> Load switch PWM 	General Features <p>$V_{DS} = -40V$ $I_D = -7.5A$</p> <p>$R_{DS(ON)} = 32\text{ m}\Omega$ @ $V_{GS} = -10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
--	--



Marking: 08P04 OR 040

Absolute Maximum Ratings: ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $TC=25^\circ\text{C}$	-7.5	A
	Continuous Drain Current- $TC=100^\circ\text{C}$	-5.7	
	Pulsed Drain Current ¹	-15	
E_{AS}	Single Pulse Avalanche Energy	36	mJ
P_D	Power Dissipation	3.1	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
R_{eJC}	Thermal Resistance,Junction to Case	40	$^\circ\text{C}/\text{W}$
R_{eJA}	Thermal Resistance,Junction to Ambient	85	

TM4907
P-Channel Enhancement Mosfet

Electrical Characteristics: ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250 \mu A$	-40	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=-32V, T_J=25^\circ C$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250 \mu A$	-1.0	---	-2.5	V
$R_{DS(ON)}$	Drain-Source On Resistance ²	$V_{GS}=-10V, I_D=-6A$	---	32	40	$m \Omega$
		$V_{GS}=-4.5V, I_D=-3A$	---	56	70	
G_{FS}	Forward Transconductance	$V_{DS}=-5V, I_D=-6A$	---	12	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$	---	1004	---	pF
C_{oss}	Output Capacitance		---	108	---	
C_{rss}	Reverse Transfer Capacitance		---	80	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DS}=-15V, V_{GS}=-10V$ $I_D=-1A, R_{GEN}=3.3 \Omega$	---	19.2	---	ns
t_r	Rise Time ^{2,3}		---	12.8	---	ns
$t_{d(off)}$	Turn-Off Delay Time ^{2,3}		---	48.6	---	ns
t_f	Fall Time ^{2,3}		---	4.6	---	ns
Q_g	Total Gate Charge ^{2,3}	$V_{DS}=-20V, V_{GS}=-4.5V,$ $I_D=-6A$	---	9	---	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	2.54	---	nC
Q_{gd}	Gate-Drain "Miller" Charge ^{2,3}		---	3.1	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ C$	---	---	-1	V
L_S	Continuous Source Current1,5	$V_G=V_D=0V$, Force Current	---	---	-7.5	
L_{SM}	Pulsed Source Current2,5		---	---	-15	

- Notes:**
- Repetitive Rating : Pulsed width limited by maximum junction temperature.
 - The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - Essentially independent of operating temperature.

Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

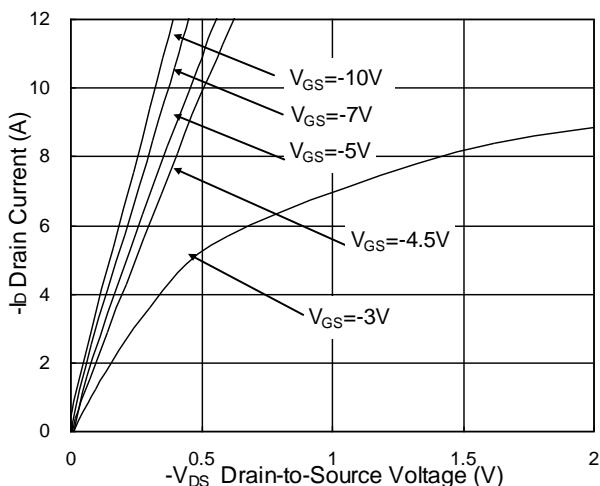


Fig.1 Typical Output Characteristics

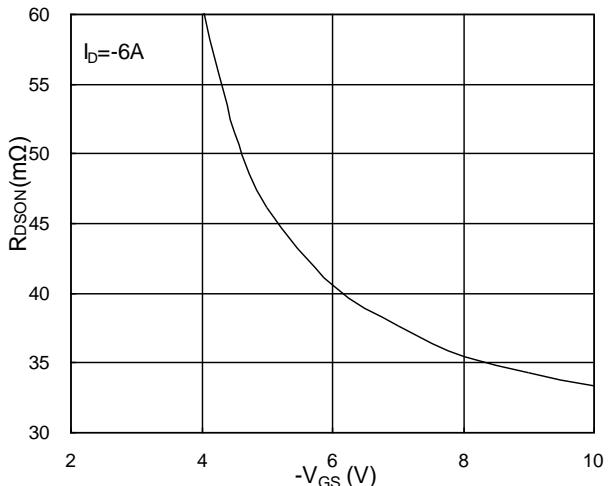


Fig.2 On-Resistance v.s Gate-Source

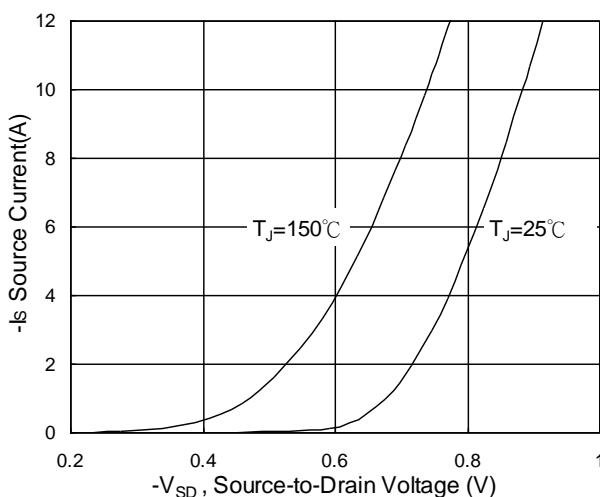


Fig.3 Forward Characteristics of Reverse

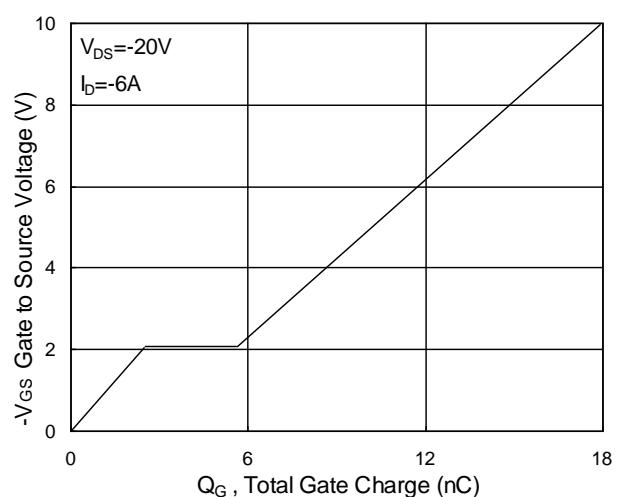


Fig.4 Gate-Charge Characteristics

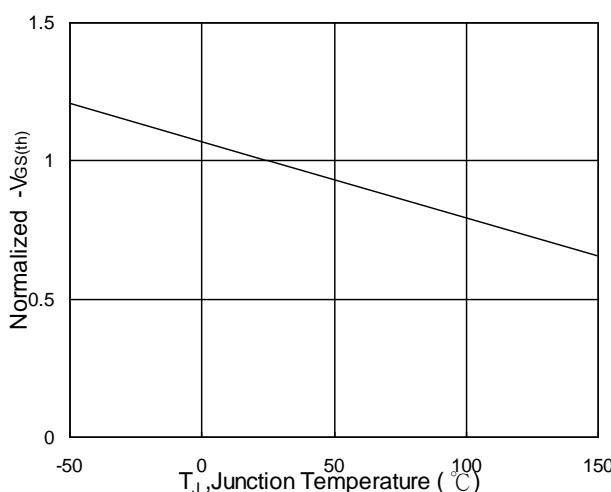


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

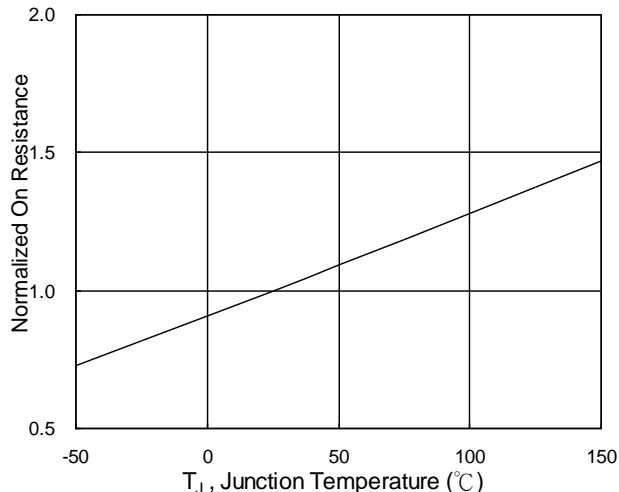


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

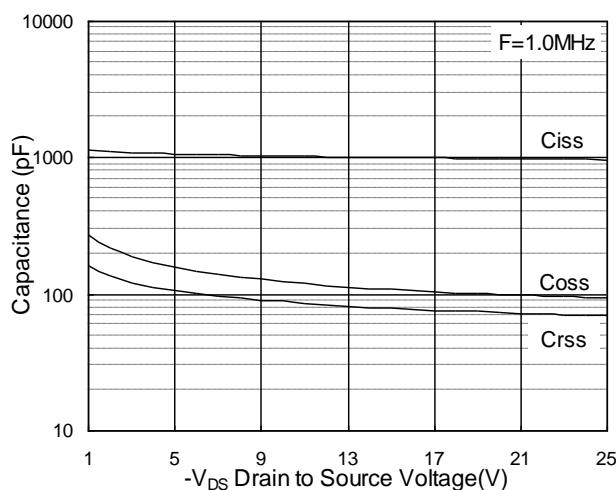


Fig.7 Capacitance

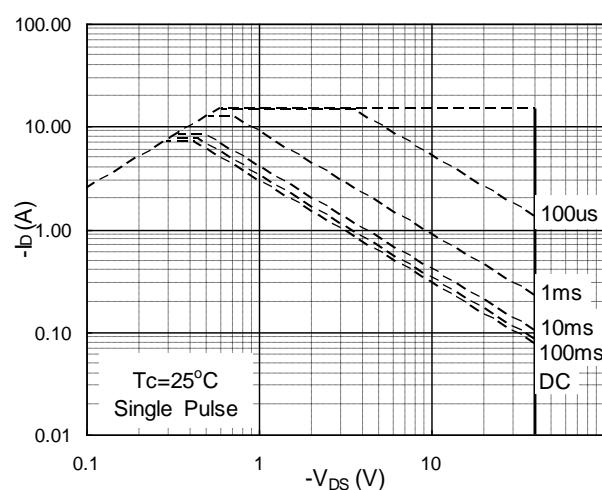


Fig.8 Safe Operating Area

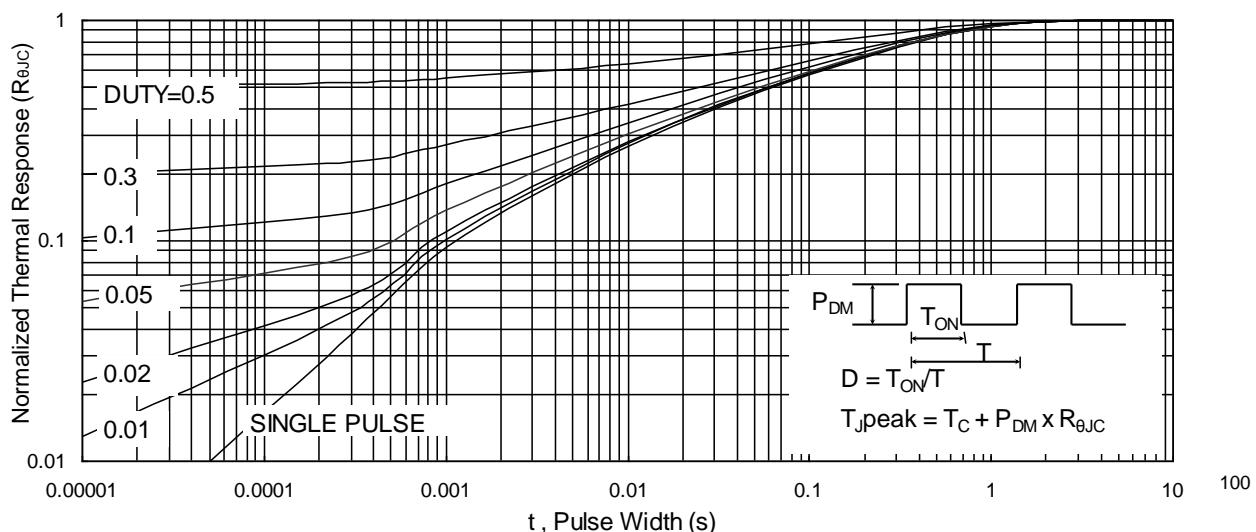


Fig.9 Normalized Maximum Transient Thermal Impedance

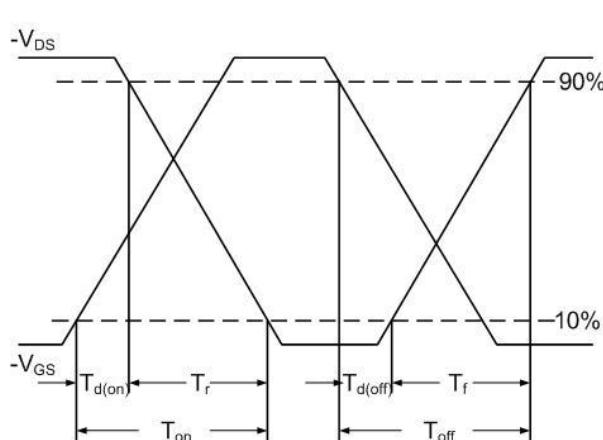


Fig.10 Switching Time Waveform

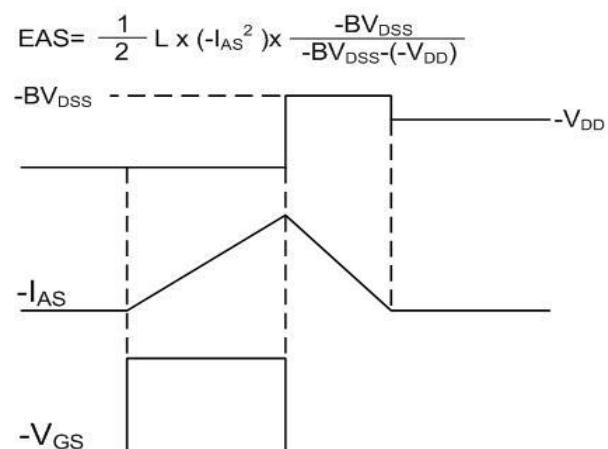
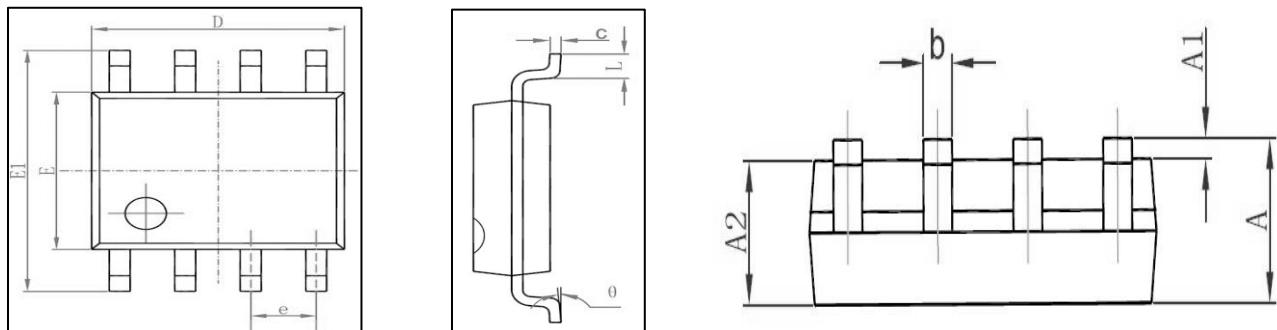
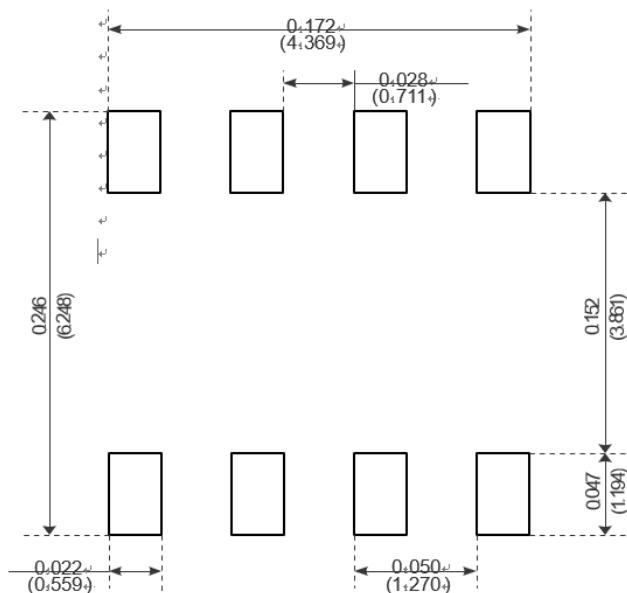


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



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